



### 600V N-Channel MOSFET

### 1N60

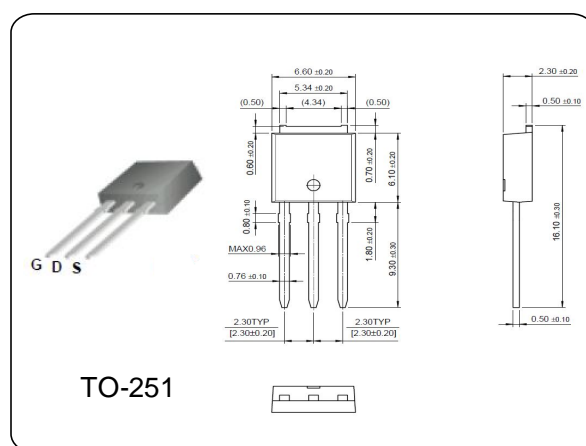
#### DESCRIPTION

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply.

#### ABSOLUTE MAXIMUM RATINGS ( Ta = 25 °C)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	600	V
Drain Current - Continuous	$I_D$	1.0	A
Drain Current - Pulsed	$I_{DM}$	4.0	A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Power Dissipation	$P_D$	30	W
Max. Operating Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~150	°C



#### ELECTRICAL CHARACTERISTICS ( Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250 \mu A$	600	—	—	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 600V, V_{GS} = 0V$	—	—	10	uA
Gate-Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS} = 30V, V_{DS} = 0V$	—	—	100	nA
Gate-Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS} = -30V, V_{DS} = 0V$	—	—	-100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0	—	5.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10 V, I_D = 0.5 A$	—	9.3	11.5	W
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0 V, I_S = 1.0 A$	—	—	1.4	V